

JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO.,LTD

TO-92 Plastic-Encapsulate Transistors

\$8050 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 0.625 W (Tamb=25°C)

Collector current

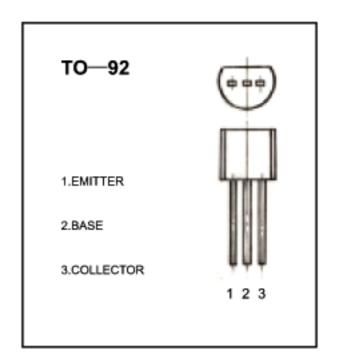
I_{CM} : 0.5 A

Collector-base voltage

V_{(BR)CBO}: 40 V

Operating and storage junction temperature range

 T_J , T_{stg} : -55 $^{\circ}$ C to +150 $^{\circ}$ C



ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR) _{CB}	Ic= 100 μ A , I _E =0	40			٧
Collector-emitter breakdown voltage	V(BR) _{CE}	Ic= 0.1 mA , I _B =0	25			٧
Emitter-base breakdown voltage	V(BR) _{EB}	I _E = 100 μ A , I _C =0	5			٧
Collector cut-off current	I _{CBO}	V _{CB} = 40 V , I _E =0			0.1	μ Α
Collector cut-off current	I _{CEO}	V _{CE} = 20 V , I _B =0			0.1	μА
Emitter cut-off current	I _{EBO}	V _{EB} = -3 V, I _C =0			0.1	μ А
DC current gain	H _{FE (1)}	V_{CE} = 1 V, I_{C} = 50mA	85		300	
DC current gain	H _{FE (2)}	V_{CE} = 1 V, I_{C} = 500mA	50			
Collector-emitter saturation voltage	V _{CE} (sat)	I _C =500mA, I _B =50 mA			0.6	٧
Base-emitter saturation voltage	V _{BE} (sat)	I _C =500mA, I _B =50 mA			1.2	٧
Base-emitter voltage	V _{BE}	I _E = 100mA			1.4	٧
Transition frequency	f⊤	V_{CE} = 6 V, I_{C} =20mA f =30MHz	150			MHz

CLASSIFICATION OF H_{FE(1)}

Rank	В	С	D
Range	85-160	120-200	160-300